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(54) **Title**: DOUBLE MASK SELF-ALIGNED DOUBLE PATTERNING TECHNOLOGY (SADPT) PROCESS

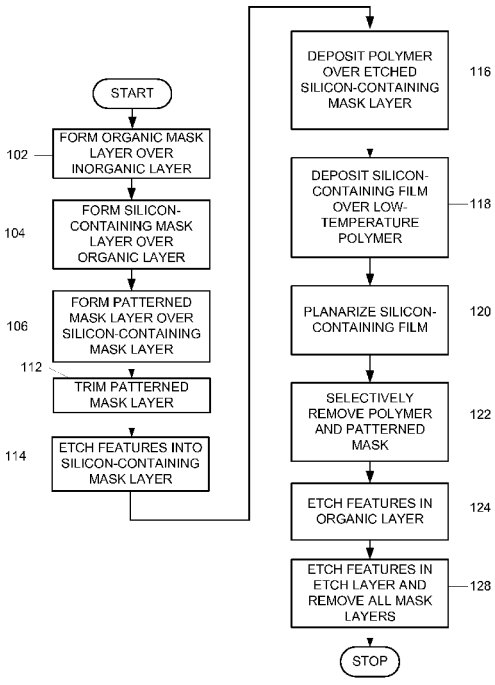


FIG. 1

(57) **Abstract**: A method for providing features in an etch layer is provided by forming an organic mask layer over the inorganic mask layer, forming a silicon-containing mask layer over the organic mask layer, forming a patterned mask layer over the silicon-containing mask layer, etching the silicon-containing mask layer through the patterned mask, depositing a polymer over the etched silicon-containing mask layer, depositing a silicon-containing film over the polymer, planarizing the silicon-containing film, selectively removing the polymer leaving the silicon-containing film, etching the organic layer, and etching the inorganic layer.

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